OPB708, OPB709 OPB740 Series, OPB740WZ Series

Features:

- · Focused for maximum sensitivity
- Phototransistor or photodarlington output
- Crosstalk does not exceed specified ICEO
- 24" (610 mm) wire length
- 26 AWG wire size



Description:

Each reflective object sensor in the **OPB708**, **OPB709**, **OPB740** through **OPB746** and **OPB740WZ** through **OPB746WZ** series consists of an infrared emitting diode and a NPN silicon phototransistor or a photodarlington. The **OPB747WZ** and **OPB748WZ** consist of a Red visible LED and a low light level rejection (R_{BE}) NPN silicon phototransistor. The Red LED allows better contrast ratio when detecting Black marks on a White surface. All these devices are mounted side-by-side on converging optical axes in a black plastic housing focusing on a small area and depth of field.

OPB7 _ _ **WZ** series are wired (UL approved wire) devices that offer various lens options, including no windows, blue polysulfone windows for dust protection or opaque aperture windows with offset openings for improved target resolution.

On each sensor included in this data sheet, the photosensor responds to radiation only when a reflective object passes within its field of view.

Custom IC(ON) current binning, special wire lengths and connectorization is available through your OPTEK rep.

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor
- Thermal Paper Mark

ONTAINS	POLYSU	JLFONE

To avoid stress cracking, we suggest using ND Industries' Vibra-Tite for thread-locking. Vibra-Tite evaporates fast without causing structural failure in OPTEK's molded plastics.

Applies to: OPB460, OPB470, OPB480, OPB490.

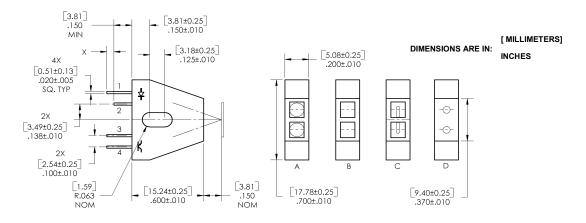


Part Number	LED Peak Wavelength	Sensor	Reflection Distance Inch (mm)	Lead Length/ Wire Type
OPB708	935 nm	Transistor		
OPB709	933 11111	Darlington		
OPB740				
OPB741				0.150"
OPB742		Transistor		Minimum
OPB743				
OPB744				
OPB745	890 nm	Darlington	Min=0.08" [2.04mm]	
OPB740WZ	890 11111		Typ=0.15" [3.81mm]	
OPB741WZ			Max=0.30" [7.62mm]	
OPB742WZ		Transistor		
OPB743WZ				24" / 26
OPB744WZ				24" / 26 AWG Wire
OPB745WZ		Darlington		AWG WIIC
OPB746WZ	935 nm	R _{BE} Transistor		
OPB747WZ	645nm	TABE TTATISTSTOT		
OPB748WZ	0431111	Transistor		

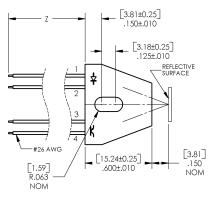
OPB708, OPB709 OPB740 Series, OPB740WZ Series

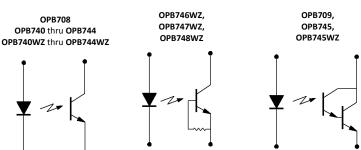


OPB708, OPB709, OPB740, OPB741, OPB742, OPB743, OPB744, OPB745



OPB740WZ, OPB741WZ, OPB742WZ, OPB743WZ, OPB744WZ, OPB745WZ, OPB746WZ, OPB747WZ, OPB748WZ





Color-PIN #	LED	Color-PIN #	Transistor
Orange-1	Anode	White-4	Collector
Green-2	Cathode	Blue-3	Emitter

Packa	ge Style
Part Number	Lens Configuration
OPB708	D - No windows
OPB709	D - No windows
OPB740	A - No windows
OPB740WZ	A - No windows
OPB741	B - Blue windows
OPB741WZ	B - Blue windows
OPB742	C - Offset windows
OPB742WZ	C - Offset windows
OPB743	A - No windows
OPB743WZ	A - No windows
OPB744	B - Blue windows
OPB744WZ	B - Blue windows
OPB745	C - Offset windows
OPB745WZ	C - Offset windows
OPB746WZ	B - Blue windows
OPB747WZ	C - Offset windows
OPB748WZ	C - Offset windows

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OPB708, OPB709 OPB740 Series, OPB740WZ Series



Absolute Maximum Ratings (T _A = 25° C unless otherwise noted)						
Operating and Storage Temperature Range						
OPB708, OP709, OPB740, OPB741, OPB742, OPB743, OPB744, OPB745	-40° C to +85° C					
OPB741WZ, OPB742WZ, OPB743WZ, OPB744WZ, OPB745WZ, OPB746WZ, OPB747WZ, OPB748WZ	-40° C to +80° C					
Lead Soldering Temperature [1/16 inch (1.6mm) from the case for 5 sec. with soldering iron] ⁽¹⁾	260°C					
Input Diode (See OP165 (935 nm), OP265 (890 nm) or OVLAS6CB8 (645 nm) for additional information)						
Forward DC Current	40 mA					
Reverse DC Voltage	2 V					
Power Dissipation ⁽²⁾	100 mW					
Sensor Output (See OP505 (Transistor), OP705 (R _{BE} Transistor) or OP535 (Darlington) for additional Information)						
Collector-Emitter Voltage						
OPB708	30 V					
OPB709	15 V					
OPB740, OPB741, OPB742, OPB743, OPB744	30 V					
OPB740WZ, OPB741WZ, OPB742WZ, OPB743WZ, OPB744WZ OPB748WZ	30 V					
OPB745	15 V					
OPB745WZ	15 V					
OPB746WZ, OPB747WZ	24 V					
Emitter-Collector Voltage						
OPB708 through OPB745, OPB748	5.0 V					
OPB746 through OPB747	0.4 V					
Power Dissipation ⁽²⁾	100 mW					

Notes:

- 1. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 2. Derate linearly 1.33 mW° C above 25° C.

Electrical	Characteristics (T _A = 25° C unless other	vise not	ed)			
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
645 nm LE	D (See OVLAS6CB8 for generic information $-$ for	referen	ce only)			
V_{F}	Forward Voltage	-	-	2.6	V	I _F = 20 mA
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V
890 nm LE	D (See OP265 for additional information — for re	eference	only)			
V_{F}	Forward Voltage	-	-	1.8	V	I _F = 40 mA
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V
935 nm LE	f D (See OP165 for additional information $-$ for re	ference	only)			
V_{F}	Forward Voltage	-	-	1.7	V	I _F = 40 mA
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V

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OPB708, OPB709





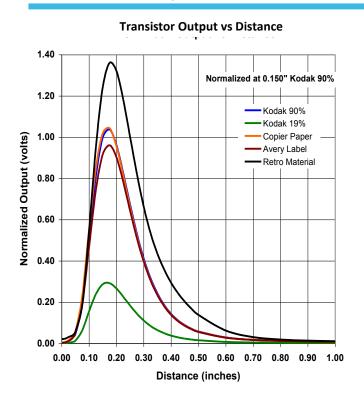
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
						TEST CONDITIONS
Output R _{BE}	Phototransistor (See OP705 for general inf	ormation -	– tor ret	erence o	nly)	I
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	24	-	-	V	Ι _C = 100 μΑ
I _{CEO}	Collector Dark Current	-	-	100	nA	$V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$
Output Pho	totransistor (See OP505 for general inform	ation — fo	r refere	nce only)		
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	Ι _C = 100 μΑ
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	Ι _Ε = 100 μΑ
I _{CEO}	Collector Dark Current	-	-	100	nA	V _{CE} = 10 V, I _F = 0, E _E =0
Output Pho	todarlington (See OP535 for general inforr	nation — f	or refere	ence only	·)	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	15	-	-	V	Ι _C = 100 μΑ
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	_	-	V	Ι _Ε = 100 μΑ
	Collector-Emitter Dark Current					
I _{CEO}	OPB709, OPB745, OPB745WZ	-	-	25	μΑ	$V_{CE} = 5 \text{ V}, I_F = 0, E_E = 0$
Coupled						
	Saturation Voltage					
$V_{CE(SAT)}$	OPB708	-	-	0.40	v	$I_F = 40 \text{ mA}, I_c = 3 \mu\text{A}, d = 0.15''^{(1)(2)}$
	OPB709	-	-	1.10	v	11 40 IIIA, 1 _C - 3 μA , α - 0.13
	On-State Collector Current					
	OPB708	0.01	-	3.00		
	OPB709	1.00	-	-		
	OPB740, OPB740WZ	0.05	-	2.50		
	OPB741, OPB741W Z	0.05	-	2.50		
$I_{C(ON)}^{(1)(2)}$	OPB742, OPB742WZ	0.01	-	0.70	mA	$V_{CE} = 5 \text{ V}, I_F = 40 \text{mA},$
C(ON)	OPB743, OPB743WZ	0.20	-	2.00		d = 0.15" (3.810 mm)
	OPB744, OPB744WZ	0.20	-	2.00		
	OPB745, OPB745WZ	5.00	-	26.0		
	OPB746WZ	0.50	-	2.50		
	OPB747WZ	0.01	-	0.70		
	OPB748WZ	0.01	-	0.70		
	Crosstalk					
	OPB708, OPB709,	-	-	-		
	OPB740, OPB740WZ	-	-	10.0		
	OPB741, OPB741WZ	-	-	10.0		
	OPB742, OPB742WZ	-	-	1.0	μΑ	
$I_{CX}^{(3)}$	OPB743, OPB743WZ	-	-	20.0		N 5 N 1 40 1
	OPB744, OPB744WZ	-	-	20.0		$V_{CC} = 5 \text{ V, } I_F = 40\text{mA}$
	OPB745, OPB745WZ	-	-	25.0		
	OPB746WZ	-	-	1.0		
	OPB747WZ	-	-	1.0		
	OPB748WZ		_	1.0		

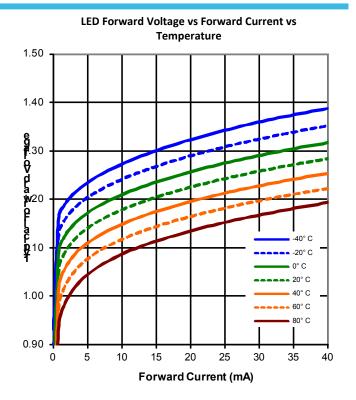
Notes:

- The distance from the assembly face to the reflective surface is "d".
- 2. Reflective surface is Eastman Kodak (Catalog #190 3061) neutral white test card with 90% diffuse reflectance as a reflecting surface.
- Reflective surface is Eastman Rodak (Catalog #350 3007) Neutral white Cost card with 30% amase reflectance as a reflecting $E_{\rm E} = 0$). Crosstalk is the photocurrent measured with current to the input diode, no reflective surface and no ambient light ($E_{\rm E} = 0$).

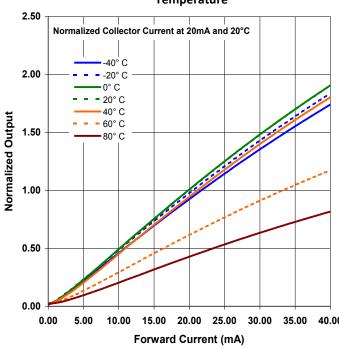
OPB708, OPB709 OPB740 Series, OPB740WZ Series





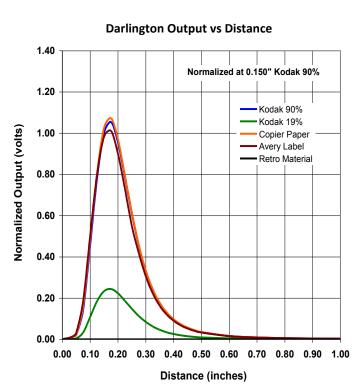


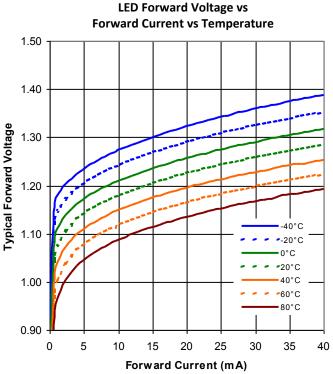
Transistor Output vs Forward Current vs Temperature



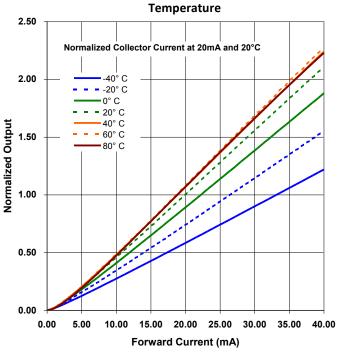
OPB708, OPB709 OPB740 Series, OPB740WZ Series







Darlington Output vs Forward Current vs



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